



FDB2614

N-Channel PowerTrench® MOSFET

200 V, 62 A, 27 mΩ

Features

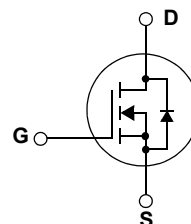
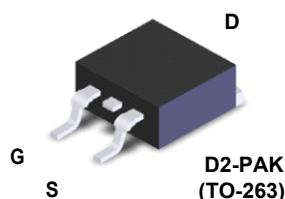
- $R_{DS(on)} = 22.9 \text{ m}\Omega$ (Typ.) @ $V_{GS} = 10 \text{ V}$, $I_D = 31 \text{ A}$
- High Performance Trench Technology for Extremely Low $R_{DS(on)}$
- Low Gate Charge
- High Power and Current Handling Capability

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's PowerTrench® process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification
- Battery Protection Circuit
- Motor drives and Uninterruptible Power Supplies



Absolute Maximum Ratings

Symbol	Parameter	FDB2614	Unit
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 30	V
I_D	Drain Current - Continuous ($T_C = 25^\circ\text{C}$) - Continuous ($T_C = 100^\circ\text{C}$)	62 39.3	A A
I_{DM}	Drain Current - Pulsed (Note 1)	see Figure 9	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)	145	mJ
dv/dt	Peak Diode Recovery dv/dt (Note 3)	4.5	V/ns
P_D	Power Dissipation ($T_C = 25^\circ\text{C}$) - Derate above 25°C	260 2.1	W W/ $^\circ\text{C}$
T_J, T_{STG}	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
T_L	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

*Drain current limited by maximum junction temperature

Thermal Characteristics

Symbol	Parameter	FDB2614	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.48	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	$^\circ\text{C/W}$
$R_{\theta JA}^*$	Thermal Resistance, Junction-to-Ambient, Max. *	62.5	$^\circ\text{C/W}$

*When mounted on the minimum pad size recommended (PCB Mount)

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDB2614	FDB2614	D ² -PAK	330mm	24mm	800

Electrical Characteristics T_C = 25°C unless otherwise noted

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 250μA, T _J = 25°C	200	--	--	V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	--	0.2	--	V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 200V, V _{GS} = 0V V _{DS} = 200V, V _{GS} = 0V, T _J = 125°C	-- --	-- --	1 500	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30V, V _{DS} = 0V	--	--	100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30V, V _{DS} = 0V	--	--	-100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250μA	3.0	4.0	5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10V, I _D = 31A	--	22.9	27	mΩ
g _{FS}	Forward Transconductance	V _{DS} = 10V, I _D = 31A	--	72	--	S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 25V, V _{GS} = 0V f = 1.0MHz	--	5435	7230	pF
C _{oss}	Output Capacitance		--	505	675	pF
C _{rss}	Reverse Transfer Capacitance		--	110	165	pF
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 100V, I _D = 62A V _{GS} = 10V, R _{GEN} = 25Ω (Note 4)	--	77	165	ns
t _r	Turn-On Rise Time		--	284	560	ns
t _{d(off)}	Turn-Off Delay Time		--	103	220	ns
t _f	Turn-Off Fall Time		--	162	335	ns
Q _g	Total Gate Charge	V _{DS} = 100V, I _D = 62A V _{GS} = 10V (Note 4)	--	76	99	nC
Q _{gs}	Gate-Source Charge		--	35	--	nC
Q _{gd}	Gate-Drain Charge		--	18	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain-Source Diode Forward Current		--	--	62	A
I _{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	186	A
V _{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0V, I _S = 62A	--	--	1.2	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _S = 62A dI _F /dt =100A/μs	--	145	--	ns
Q _{rr}	Reverse Recovery Charge		--	0.81	--	μC

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature
2. L = 1mH, I_{AS} = 17A, V_{DD} = 50V, R_G = 25Ω, Starting T_J = 25°C
3. I_{SD} ≤ 62A, di_F/dt ≤ 100A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Essentially Independent of Operating Temperature Typical Characteristics

Figure 1. On-Region Characteristics

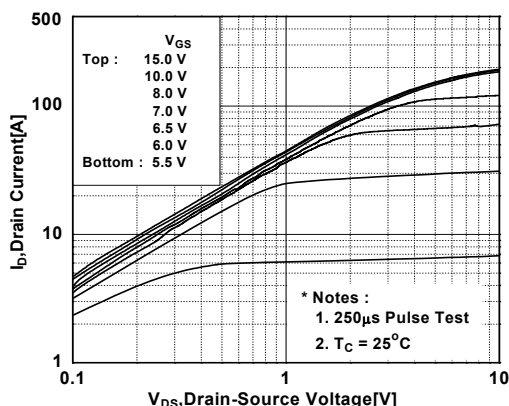


Figure 2. Transfer Characteristics

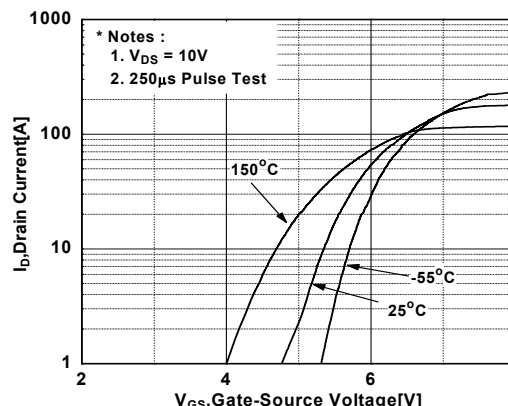


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

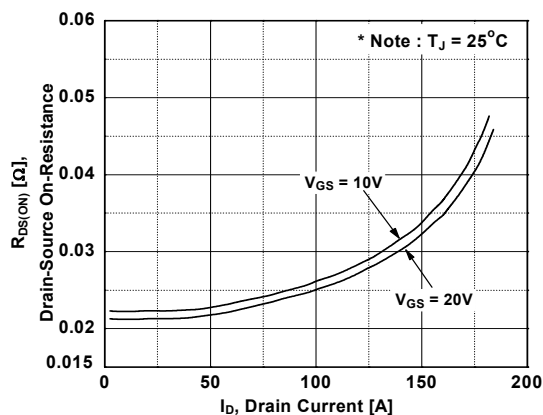


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

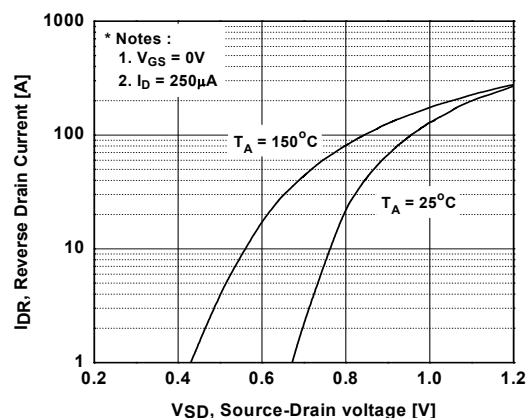


Figure 5. Capacitance Characteristics

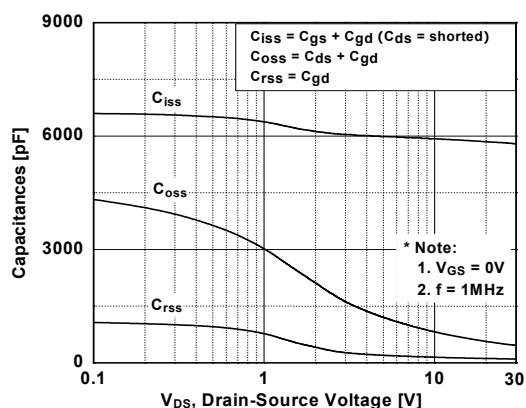


Figure 6. Gate Charge Characteristics

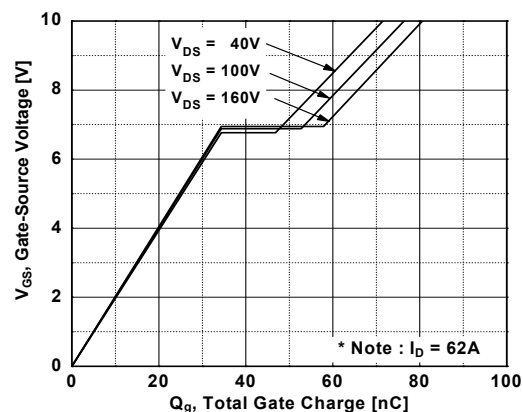


Figure 7. Breakdown Voltage Variation vs. Temperature

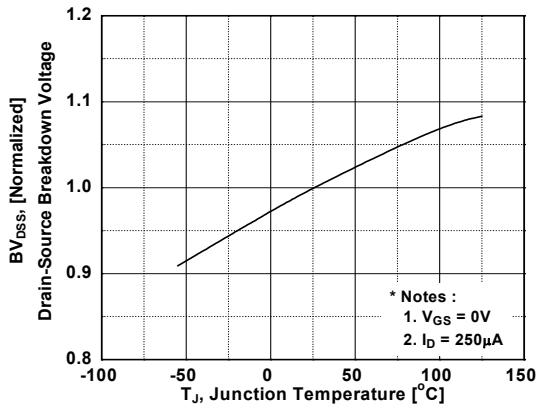


Figure 8. On-Resistance Variation vs. Temperature

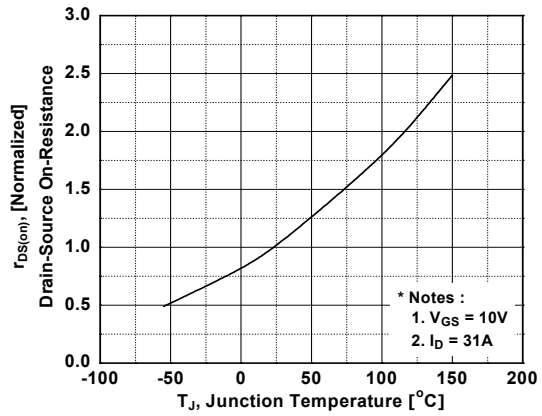


Figure 9. Maximum Safe Operating Area

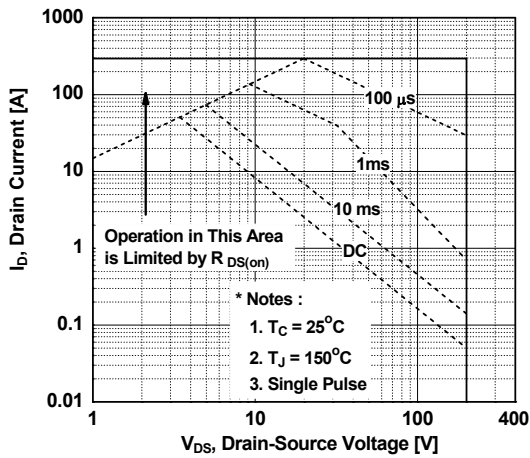


Figure 10. Maximum Drain Current vs. Case Temperature

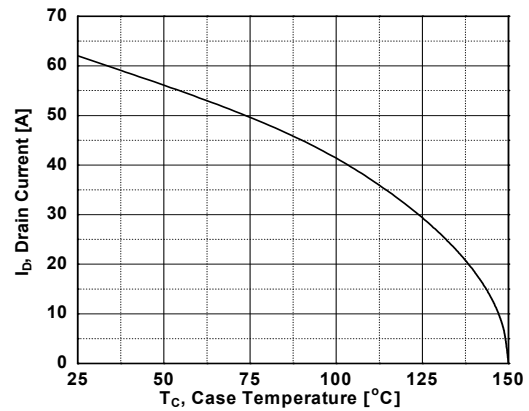
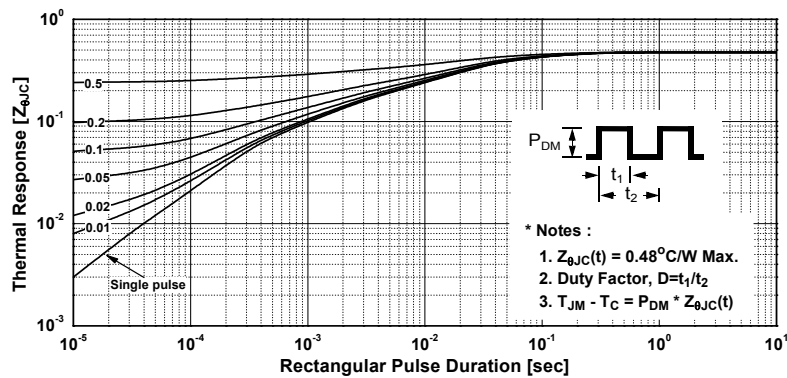
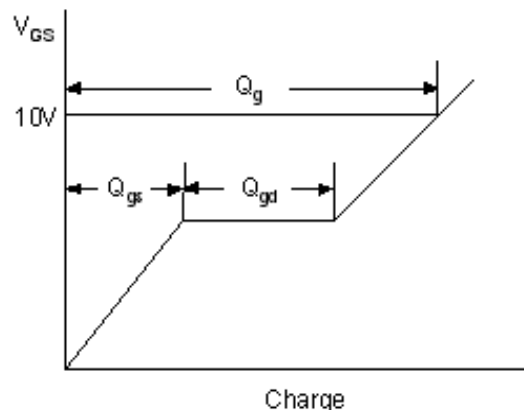
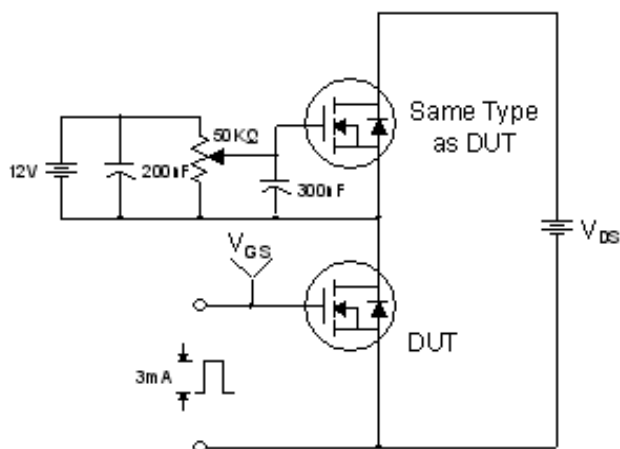


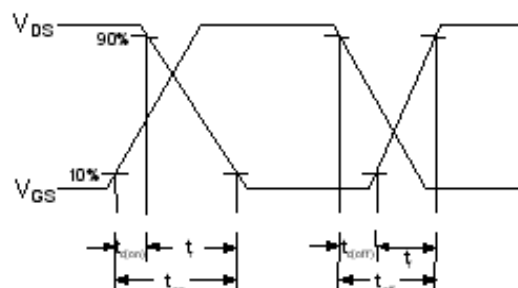
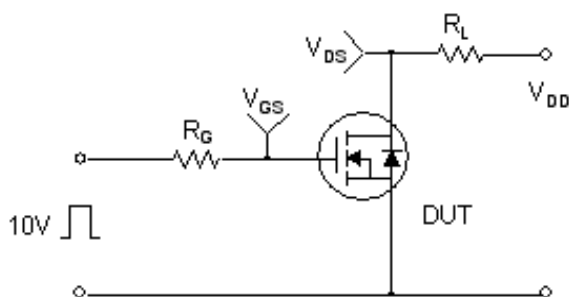
Figure 11. Transient Thermal Response Curve



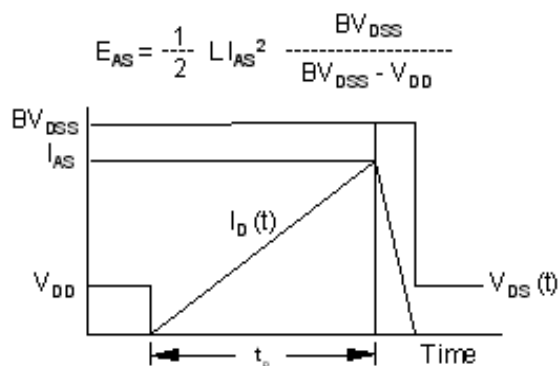
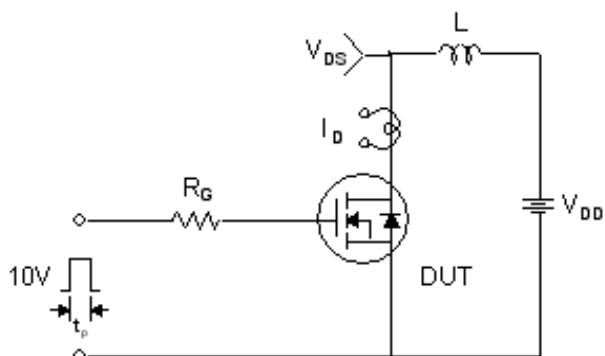
Gate Charge Test Circuit & Waveform

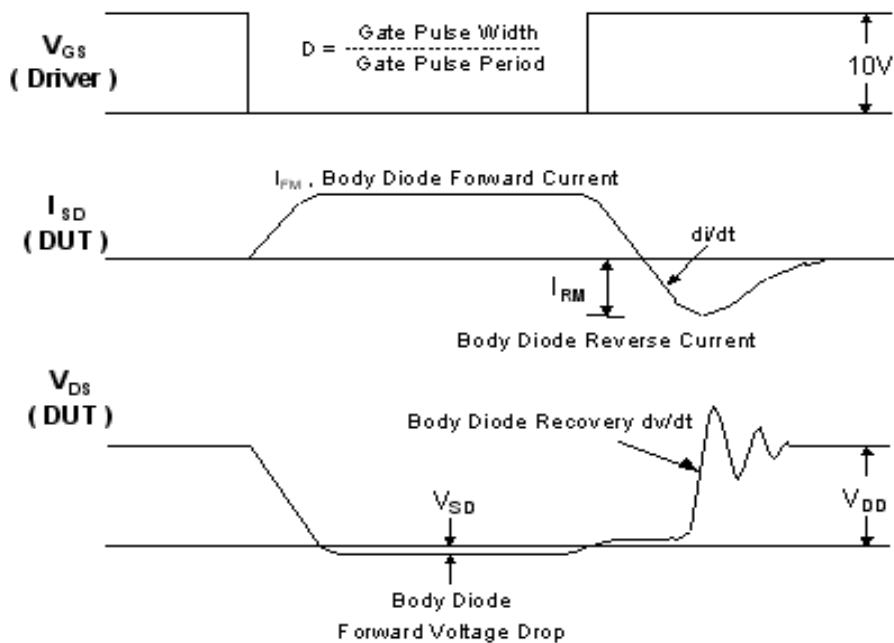
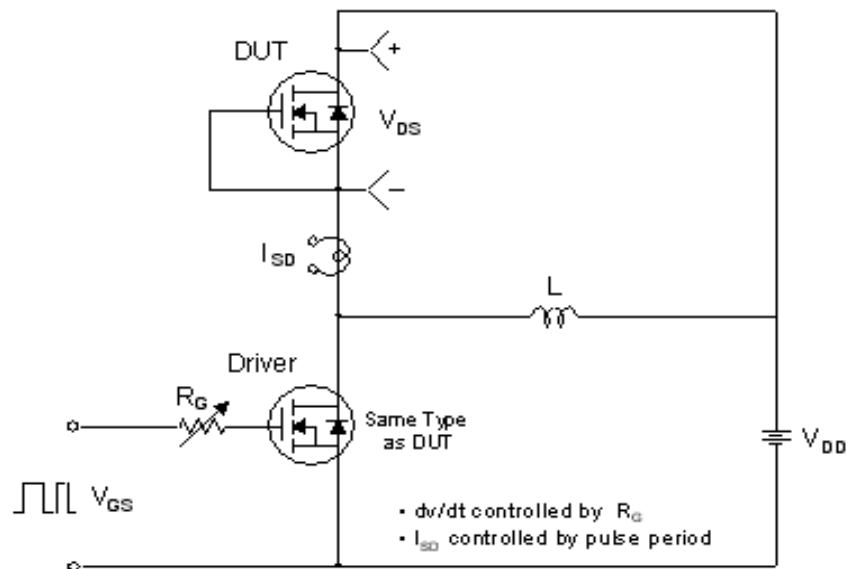


Resistive Switching Test Circuit & Waveforms



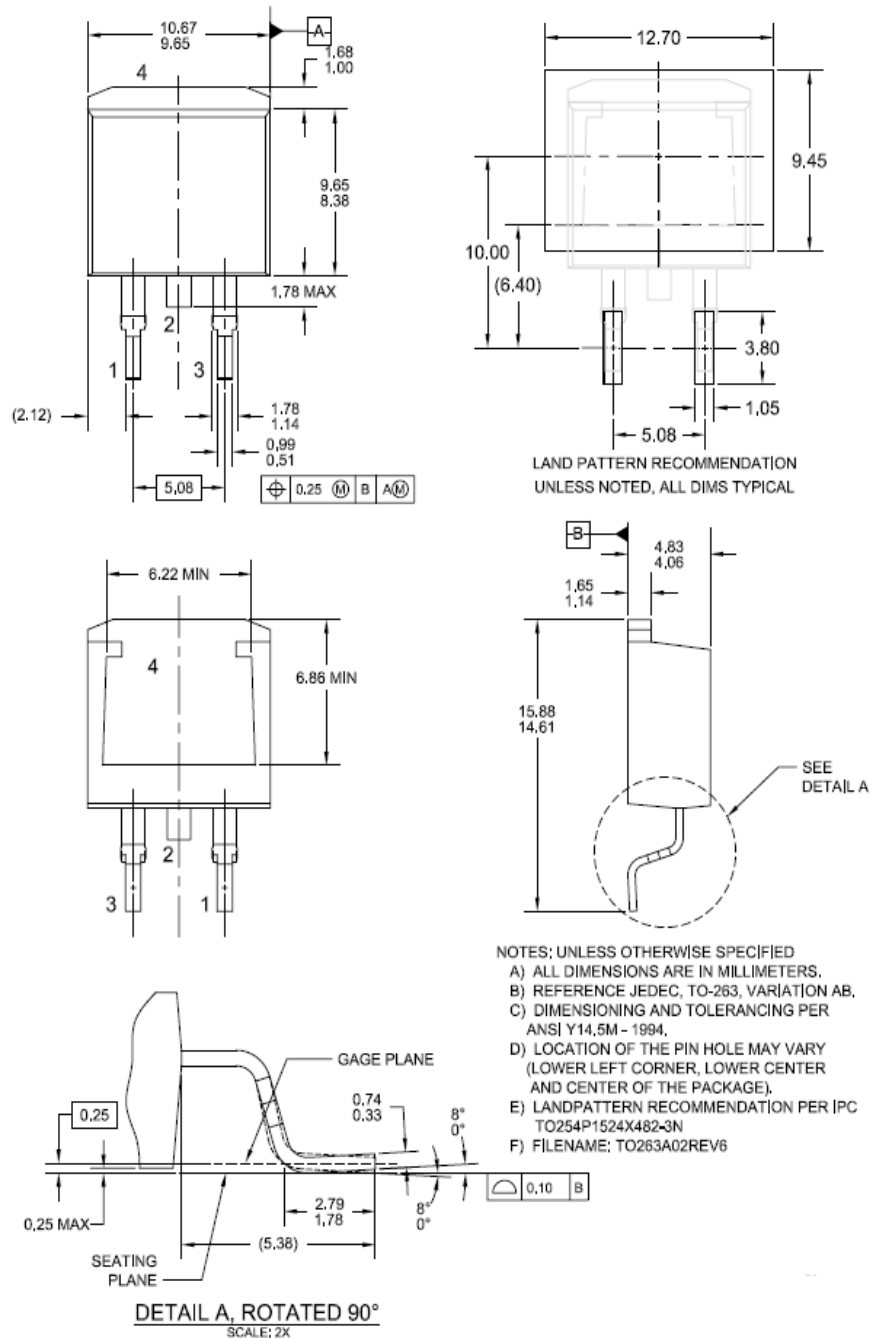
Unclamped Inductive Switching Test Circuit & Waveforms



Peak Diode Recovery dv/dt Test Circuit & Waveforms

Mechanical Dimensions

D²-PAK



Dimensions in Millimeters

